

IN UNITED STATES PATENT AND TRADEMARK OFFICE

Patent No.: 7,250,319

Docket No: 8346/ETCH/CONE

Issue Date: July 31, 2007

Patentee: Liu, et al.

Title

METHOD OF FABRICATING QUANTUM FEATURES

REQUEST FOR CERTIFICATION OF CORRECTION

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

It is requested that a Certificate of Correction be issued correcting printing errors appearing in the above-identified United States patent. A copy of the text of the Certificate in the suggested form is enclosed.

The fee of \$100.00 has been paid with the submission of this paper using the Patent Electronic Business Center. The Commissioner is authorized to charge any additional fees to Deposit Account No. 20-0782.

Issuance of the Certificate of Correction would neither expand nor contract the scope of the claims as properly allowed, and re-examination is not required.

Respectfully submitted,

Nov 1, 2007


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UNITED STATES PATENT AND TRADEMARK OFFICE
CERTIFICATE OF CORRECTION

PATENT NO : 7,250,319

DATED : July 31, 2007

INVENTOR(S) : Liu et al.

It is certified that errors appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

On the face page, in field (57), in "Abstract", in column 2, line 3, delete "InP," and insert - - InP, --, therefor.

In column 6, line 9, delete "FIG. 21" and insert - - FIG. 2I --, therefor.

In column 6, line 11, after "step 106." insert - - The elongated features 220 have a distance about 110 nm or greater from one another. --.

In column 6, lines 21-29, delete "At step 116, the first hard mask layer 206 is removed. The cross-sectional and top plan views of the substrate 200 having the elongated features 220 (e.g., silicon elongated structures) formed on the barrier layer 202 are depicted in FIG. 21 and FIG. 2I, respectively. In one exemplary embodiment, to remove the .alpha.-carbon layer 206, step 116 may use the process described above in reference to step 106. The elongated features 220 have a distance about 110 nm or greater from one another." and
insert - - At step 118, if the method is being used for creating quantum dots, a second hard mask layer 216 and a second cap layer 218 are sequentially deposited over the elongated feature 220 and barrier layer 202 (FIG. 2K). Generally, the first and second hard mask layers 206, 216 and the first and second cap layers 208, 218 are correspondingly formed from same materials, e.g., α -carbon and silicon oxynitride, respectively. --, therefor.

In column 7, line 3, delete "(FIG. 20)" and insert - - (FIG. 2O) --, therefor.

In column 10, line 6, in Claim 11, delete "InP," and insert - - InP, --, therefor.

In column 10, line 21, in Claim 19, delete "quantom" and insert - - quantum --, therefor.

In column 10, line 23, in Claim 20, delete "quantom" and insert - - quantum --, therefor.

In column 10, line 24, in Claim 20, after "formed" insert - - in --.

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CERTIFICATE OF CORRECTION

PATENT NO : 7,250,319

DATED : July 31, 2007

INVENTOR(S) : Liu et al.

It is certified that errors appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

In column 10, line 32, in Claim 21, after "structure" delete "from".

In column 12, line 11, in Claim 42, after "comprises" insert - - : - -.

In column 12, line 45, in Claim 56, delete "claim 51," and insert - - claim 21, - -, therefor.

In column 12, line 45, in Claim 56, delete "quantom" and insert - - quantum - -, therefor.

In column 12, line 47, in Claim 57, delete "claim 51," and insert - - claim 21, - -, therefor.

In column 12, line 47, in Claim 57, delete "quantom" and insert - - quantum - -, therefor.

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